

ABSTRACT

A p-channel MOSFET (1) includes a semiconductor substrate (2), an epitaxial region (3), a second diffusion region (6), and a drain region. The epitaxial region (3) is formed on the upper surface of the semiconductor substrate (2). The second diffusion region (6) is formed in a predetermined upper surface area of the epitaxial region (3). The second diffusion region (6) has a central portion (6a) and a peripheral portion (6b). The central portion (6a) is formed substantially at the center of the epitaxial region (3) and formed thicker than the peripheral portion (6b). The peripheral portion (6b) is formed in an annular shape so as to surround the central portion (6a). The drain region 10 (7) is formed in an upper surface area of the central portion (6a) of the second diffusion region (6).